New Jersey Semi-Conductor Products, Inc.

20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A.

## Designer's™ Data Sheet **TMOS E-FET** ™ **Power Field Effect Transistor** N-Channel Enhancement-Mode Silicon Gate

This high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage–blocking capability without degrading performance over time. In addition, this advanced TMOS E–FET is designed to withstand high energy in the avalanche and commutation modes. The new energy efficient design also offers a drain–to–source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional safety margin against unexpected voltage transients.

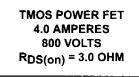
- Robust High Voltage Termination
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- IDSS and VDS(on) Specified at Elevated Temperature

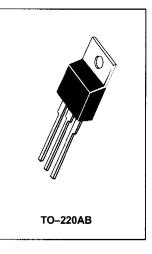


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## **MAXIMUM RATINGS** (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Source Voltage	VDSS	800	Vdc
Drain–Gate Voltage ( $R_{GS}$ = 1.0 M $\Omega$ )	VDGR	800	Vdc
Gate–Source Voltage — Continuous — Non–Repetitive (t <sub>p</sub> ≤ 10 ms)	V <sub>GS</sub> VGSM	± 20 ± 40	Vdc Vpk
Drain Current — Continuous — Continuous @ 100°C — Single Pulse (t <sub>p</sub> ≤ 10 μs)	lD ID МФI	4.0 2.9 12	Adc Apk
Total Power Dissipation Derate above 25°C	۴ <sub>D</sub>	125 1.0	Watts W/°C
Operating and Storage Temperature Range	TJ, Tstg	-55 to 150	°C
Single Pulse Drain-to-Source Avalanche Energy — Starting T <sub>J</sub> = $25^{\circ}$ C (V <sub>DD</sub> = 100 Vdc, V <sub>GS</sub> = 10 Vdc, I <sub>L</sub> = 8.0 Apk, L = 10 mH, R <sub>G</sub> = $25 \Omega$ )	EAS	320	mJ
Thermal Resistance — Junction to Case — Junction to Ambient	R <sub>0JC</sub> R <sub>0JA</sub>	1.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	TL	260	°C



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## **Quality Semi-Conductors**

## MTP4N80E

$ \begin{array}{ c c c c c } \hline Gate Threshold Voltage (V_{DS} = V_{GS}, Ip = 250 \ \mu Adc) \\ Temperature Coefficient (Negative) \\ \hline Static Drain–Source On–Resistance (V_{GS} = 10 \ Vdc, \ Ip = 2.0 \ Adc) \\ \hline Drain–Source On–Voltage (V_{GS} = 10 \ Vdc) \\ (Ip = 4.0 \ Adc) \\ (Ip = 4.0 \ Adc) \\ (Ip = 2.0 \ Adc, \ T_J = 125^{\circ}C) \\ \hline \hline \\ Forward Transconductance (V_{DS} = 15 \ Vdc, \ Ip = 2.0 \ Adc) \\ \hline \\ Forward Transconductance (V_{DS} = 15 \ Vdc, \ Ip = 2.0 \ Adc) \\ \hline \\ Forward Transconductance (V_{DS} = 15 \ Vdc, \ Ip = 2.0 \ Adc) \\ \hline \\ Portal Capacitance \\ \hline \\ \hline Dutput Capacitance \\ \hline \\ \hline \\ Output Capacitance \\ \hline \\ Reverse Transfer Capacitance \\ \hline \\ \hline \\ Turn–On Delay Time \\ Rise Time \\ \hline \\ Turn–On Delay Time \\ (V_{DD} = 400 \ Vdc, \ Ip = 4.0 \ Adc, \\ V_{GS} = 10 \ Vdc, \\ R_G = 9.1 \ \Omega) \\ \hline \\ \hline \\ \hline \\ Fall Time \\ \hline \\ \hline \\ \hline \\ Gate Charge \\ (See Figure 8) \\ \hline \\ $	Тур	Typ Max	Unit
	1	I	
	1.02		Vdc mV/°C
ON CHARACTERISTICS (1)VGS(th)2.0 Gate Threshold Voltage (VDS = VGS, the 250 µAdc) Temperature Coefficient (Negative)VGS(th)2.0 	=	— 10 — 100	μAdc
$ \begin{array}{ c c c c } \hline Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 \ \mu Adc) \\ \hline Temperature Coefficient (Negative) \\ \hline Static Drain–Source On–Resistance (V_{GS} = 10 \ Vdc, I_D = 2.0 \ Adc) \\ \hline Drain–Source On–Voltage (V_{GS} = 10 \ Vdc) \\ (I_D = 4.0 \ Adc) \\ (I_D = 4.0 \ Adc) \\ (I_D = 4.0 \ Adc) \\ (I_D = 2.0 \ Adc, T_J = 125^{\circ}C) \\ \hline \hline Forward Transconductance (V_{DS} = 15 \ Vdc, I_D = 2.0 \ Adc) \\ \hline Prive Character ISTICS \\ \hline Input Capacitance \\ \hline Output Capacitance \\ \hline Output Capacitance \\ \hline Output Capacitance \\ \hline Turn–On Delay Time \\ Rise Time \\ \hline Turn–On Delay Time \\ (V_{DD} = 400 \ Vdc, I_D = 4.0 \ Adc, V_{GS} = 0 \ Vdc, R_G = 9.1 \ \Omega) \\ \hline Fall Time \\ \hline Fall Time \\ \hline Fall Time \\ \hline Gate Charge \\ (See Figure 8) \\ \hline (V_{DS} = 400 \ Vdc, I_D = 4.0 \ Adc, V_{GS} = 10 \ Vdc) \\ \hline I_S = 4.0 \ Adc, V_{GS} = 0 \ Vdc, I_J = 125^{\circ}C) \\ \hline \hline Forward On–Voltage (1) \\ \hline (I_S = 4.0 \ Adc, V_{GS} = 0 \ Vdc) \\ \hline (I_S = 4.0 \ Adc, V_{GS} = 0 \ Vdc, I_J = 125^{\circ}C) \\ \hline \hline \\ Forward On–Voltage (1) \\ \hline (I_S = 4.0 \ Adc, V_{GS} = 0 \ Vdc, I_J = 125^{\circ}C) \\ \hline \hline \\ Reverse Recovery Time \\ \hline \\ Reverse Recovery Stored Charge \\ \hline \\ Reverse Recovery Stored Charge \\ \hline \\ \hline \\ Reverse Recovery Stored Charge \\ \hline \end{array}$	_	— 100	nAdc
	•	•	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	3.0 7.0		Vdc mV/⁰C
	1.95	1.95 3.0	Ohm
DYNAMIC CHARACTERISTICSInput Capacitance $(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, f = 1.0 \text{ MHz})$ $C_{iss}$ Output Capacitance $(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, f = 1.0 \text{ MHz})$ $C_{oss}$ Reverse Transfer Capacitance $(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, f = 1.0 \text{ MHz})$ $C_{oss}$ SWITCHING CHARACTERISTICS (2)Turn-On Delay Time $(V_{DD} = 400 \text{ Vdc}, I_D = 4.0 \text{ Adc}, V_{GS} = 10 \text{ Vdc}, R_G = 9.1 \Omega)$ $t_d(on)$ Rise Time $(V_{DS} = 400 \text{ Vdc}, I_D = 4.0 \text{ Adc}, V_{GS} = 10 \text{ Vdc})$ $t_f$ Gate Charge (See Figure 8) $(V_{DS} = 400 \text{ Vdc}, I_D = 4.0 \text{ Adc}, V_{GS} = 10 \text{ Vdc})$ $Q_T$ $Q_2$ $Q_3$ SOURCE-DRAIN DIODE CHARACTERISTICS $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc})$ $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, I_J = 125^{\circ}C)$ $V_{SD}$ Reverse Recovery Time (See Figure 14) $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, I_J = 125^{\circ}C)$ $V_{SD}$ Reverse Recovery Stored Charge $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, I_J = 125^{\circ}C)$ $V_{SD}$ Reverse Recovery Stored Charge $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, I_J = 125^{\circ}C)$ $V_{SD}$ Reverse Recovery Stored Charge $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, I_J = 125^{\circ}C)$ $V_{SD}$ $Q_{RR}$ $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, I_J = 125^{\circ}C)$ $V_{SD}$	8.24 —	8.24 12 — 10	Vdc
$\begin{array}{ c c c c c } \hline \text{Input Capacitance} & (V_{DS} = 25 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, \\ f = 1.0 \text{ MHz}) & \hline C_{iss} & - \\ \hline C_{OSS} & - \\ \hline C_{rss} & - \\ \hline C_{$	4.3	4.3 —	mhos
$ \begin{array}{ c c c c } \hline \text{Output Capacitance} & (V_{DS} = 25  \text{Vdc},  V_{GS} = 0  \text{Vdc}, \\ f = 1.0  \text{MHz}) & \hline C_{OSS} & - \\ \hline C_{rSS} & - \\ \hline \\$			L
$ \begin{array}{c c} \mbox{F} = 1.0 \ \mbox{MHz} \end{pmatrix} \end{array} \begin{array}{c c} \mbox{F} = 1.0 \ \mbox{MHz} \end{pmatrix} \end{array} \begin{array}{c c} \mbox{F} = 1.0 \ \mbox{MHz} \end{pmatrix} \end{array} \begin{array}{c c} \mbox{F} = 1.0 \ \mbox{MHz} \end{pmatrix} \begin{array}{c c} \mbox{F} = 1.0 \ \mbox{MHz} \end{pmatrix} \begin{array}{c c} \mbox{F} = 1.0 \ \mbox{MHz} \end{pmatrix} \end{array} \begin{array}{c c} \mbox{F} = 1.0 \ \mbox{MHz} \end{pmatrix} \end{array} \begin{array}{c c} \mbox{F} = 1.0 \ \mbox{MHz} \end{pmatrix} \end{array} \begin{array}{c c} \mbox{F} = 1.0 \ \mbox{MHz} \end{pmatrix} \end{array} \begin{array}{c c} \mbox{MHz} \end{pmatrix} \begin{array}{c c} \mbox{F} = 1.0 \ \mbox{MHz} \end{pmatrix} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{pmatrix} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{pmatrix} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{pmatrix} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \end{array} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \end{array} \end{array} \end{array} \begin{array}{c c} \mbox{MHz} \end{array} \end{array} \end{array} \end{array} \end{array} \end{array} \end{array} \end{array} \begin{array}$	1320	1320 2030	pF
$ \begin{array}{ c c c c } \hline Reverse Transfer Capacitance & \hline C_{rss} & - \\ \hline SWITCHING CHARACTERISTICS (2) \\ \hline Turn-On Delay Time & \\ \hline Rise Time & & & & & & & & & & & & & & & & & & &$	187	187 400	
$\begin{tabular}{ c c c c } \hline Turn-On Delay Time & $$ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $$	72	72 160	
$ \begin{array}{c} \mbox{Rise Time} & (VDD = 400 \ Vdc, \ ID = 4.0 \ Adc, \\ VGS = 10 \ Vdc, \\ RG = 9.1 \ \Omega) & tr & \\ \hline td(off) & \\ \hline td(off) & \\ \hline tf & \\ \hline tf & \\ \hline 02 & $	•	• · · · ·	•
$\begin{tabular}{ c c c c c c } \hline Turn-Off Delay Time & V_{GS} = 10 \ Vdc, \\ R_G = 9.1 \ \Omega) & t_f & \\ \hline Tall Time & t_f & \\ \hline Gate Charge \\ (See Figure 8) & (V_{DS} = 400 \ Vdc, \ I_D = 4.0 \ Adc, \\ V_{GS} = 10 \ Vdc) & \frac{Q_T & \\ Q_2 & \\ Q_3 & \\ \hline Q_3 & \\ \hline \\ \hline SOURCE-DRAIN DIODE CHARACTERISTICS & \hline \\ \hline \\ \hline \\ Forward On-Voltage (1) & (I_S = 4.0 \ Adc, \ V_{GS} = 0 \ Vdc) \\ (I_S = 4.0 \ Adc, \ V_{GS} = 0 \ Vdc, \ T_J = 125^\circ C) & - \\ \hline \\ \hline \\ \hline \\ Reverse Recovery Time \\ (See Figure 14) & (I_S = 4.0 \ Adc, \ V_{GS} = 0 \ Vdc, \\ d _S/dt = 100 \ A/\mu s) & t_f & \\ \hline $	13	13 30	ns
$\begin{tabular}{ c c c c c c } \hline Turn-Off Delay Time & $$R_G = 9.1 \Omega$) & $td(off)$ & $-$$ \\ \hline Fall Time & $$tf$ & $-$$ \\ \hline Gate Charge (See Figure 8) & $$(V_{DS} = 400 \ Vdc, \ I_D = 4.0 \ Adc, $$$ $V_{CS} = 10 \ Vdc$)$ & $$Q_T$ & $-$$ \\ \hline $Q_1$ & $-$$ \\ \hline $Q_2$ & $-$$ \\ \hline $Q_2$ & $-$$ \\ \hline $Q_3$ & $-$$ \\ \hline $Q_3$ & $-$$ \\ \hline $Q_3$ & $-$$ \\ \hline $SOURCE-DRAIN DIODE CHARACTERISTICS$ & $$$ \\ \hline $Forward On-Voltage (1)$ & $$(I_S = 4.0 \ Adc, $V_{GS} = 0 \ Vdc$)$ & $$VSD$ & $$-$$ \\ \hline $Reverse Recovery Time$ & $$(I_S = 4.0 \ Adc, $V_{GS} = 0 \ Vdc$, $T_J = 125^\circ$C$)$ & $$VSD$ & $$-$$ \\ \hline $Reverse Recovery Time$ & $$$(I_S = 4.0 \ Adc, $V_{GS} = 0 \ Vdc$, $$$ \\ $dI_S/dt = 100 \ A/\mu$$)$ & $$$ \\ \hline $the $$ $the $$ $-$$ \\ \hline $Q_{RR}$ & $-$ \\ \hline $Q_{RR}$ & $$	36	36 90	
$ \begin{array}{c c} Gate Charge \\ (See Figure 8) \\ (V_{DS} = 400 \ Vdc, \ I_{D} = 4.0 \ Adc, \\ V_{GS} = 10 \ Vdc) \\ \hline \end{array} \\ \begin{array}{c c} Q_{T} & \\ \hline Q_{1} & \\ \hline Q_{2} & \\ \hline Q_{3} & \\ \hline \end{array} \\ \hline \end{array} \\ \begin{array}{c c} SOURCE-DRAIN \ DIODE \ CHARACTERISTICS \\ \hline \end{array} \\ \hline \end{array} \\ \hline \end{array} \\ \begin{array}{c c} Forward \ On-Voltage \ (1) \\ (I_{S} = 4.0 \ Adc, \ V_{GS} = 0 \ Vdc) \\ (I_{S} = 4.0 \ Adc, \ V_{GS} = 0 \ Vdc, \ T_{J} = 125^{\circ}C) \\ \hline \end{array} \\ \hline \end{array} \\ \hline \end{array} \\ \hline \end{array} \\ \hline \begin{array}{c c} Reverse \ Recovery \ Time \\ (See \ Figure \ 14) \\ \hline \end{array} \\ \hline \end{array} \\ \hline \end{array} \\ \begin{array}{c c} I_{S} = 4.0 \ Adc, \ V_{GS} = 0 \ Vdc, \ T_{J} = 125^{\circ}C \\ \hline \end{array} \\ \hline \begin{array}{c c} I_{S} = 4.0 \ Adc, \ V_{GS} = 0 \ Vdc, \ T_{J} = 125^{\circ}C \\ \hline \end{array} \\ \hline $ \\ \hline \end{array} \\ \hline \end{array} \\ \hline \end{array} \\ \hline  \\ \hline \end{array} \\ \hline  \\ \hline \end{array} \\ \hline \end{array} \\ \hline  \\ \hline \end{array} \\ \hline \end{array} \\ \hline \end{array} \\ \hline  \\ \hline \end{array} \\ \hline  \\ \hline  \\ \hline \end{array} \\ \hline \end{array} \\ \hline \end{array} \\ \hline \end{array} \\ \hline  \\ \hline  \\ \hline \end{array} \\ \hline  \\ \hline  \\ \hline \end{array} \\ \hline  \\ \hline \end{array} \\ \hline \end{array} \\ \hline  \\ \hline \end{array} \\ \hline  \\ \\  \\ \hline  \\ \\ \end{array} \\  \\ \hline  \\ \\  \\ \hline  \\ \hline  \\ \hline  \\ \\  \\ \hline  \\ \\  \\ \hline  \\ \\ \\  \\ \hline  \\ \\ \\  \\ \hline  \\ \\  \\ \\ \\  \\ \\  \\ \\  \\ \\ \\  \\ \\ \\  \\ \\  \\ \\  \\ \\  \\ \\  \\ \\  \\ \\ \\  \\ \\  \\ \\ \\  \\ \\  \\ \\  \\ \\  \\ \\  \\ \\ \\ \\  \\ \\  \\ \\  \\ \\  \\	40	40 80	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	30	30 75	
$ \begin{array}{ c c c c c } & (V_{DS} = 400 \ Vdc, \ I_{D} = 4.0 \ Adc, \\ V_{GS} = 10 \ Vdc) & \hline & Q_{2} & \\ \hline & Q_{3} & \\ \hline & Q_$	36	36 80	nC
$V_{GS} = 10 \text{ Vdc}) \qquad \qquad$	7.0	7.0 —	
SOURCE-DRAIN DIODE CHARACTERISTICSForward On-Voltage (1) $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc})$ $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_J = 125^{\circ}C)$ $-$ $-$ Reverse Recovery Time (See Figure 14) $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_J = 125^{\circ}C)$ $t_{rr}$ $-$ Reverse Recovery Time $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_J = 125^{\circ}C)$ $t_{rr}$ $-$ Reverse Recovery Time $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_J = 125^{\circ}C)$ $t_{rr}$ $-$ Reverse Recovery Stored Charge $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_J = 125^{\circ}C)$ $t_a$ Reverse Recovery Stored Charge $(I_S = 4.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_J = 125^{\circ}C)$ $T_{rr}$	16.5	16.5 —	
$ \begin{array}{ c c c c c } \hline Forward On-Voltage (1) & (I_S = 4.0 \mbox{ Adc}, V_{GS} = 0 \mbox{ Vdc}) & VSD & - \\ \hline & (I_S = 4.0 \mbox{ Adc}, V_{GS} = 0 \mbox{ Vdc}, T_J = 125^{\circ}C) & \hline & - \\ \hline & Reverse \mbox{ Recovery Time} & (I_S = 4.0 \mbox{ Adc}, V_{GS} = 0 \mbox{ Vdc}, \\ \hline & (I_S = 4.0 \mbox{ Adc}, V_{GS} = 0 \mbox{ Vdc}, \\ \hline & dI_S/dt = 100 \mbox{ A/}\mu s) & \hline & t_a & - \\ \hline & t_b & - \\ \hline & Q_{RR} & - \\ \hline & \end{array} $	12	12	
$ \begin{array}{c} (I_{S} = 4.0 \text{ Adc}, \text{ V}_{GS} = 0 \text{ Vdc}, \text{ T}_{J} = 125^{\circ}\text{C}) \\ \hline \\ \text{Reverse Recovery Time} \\ (See Figure 14) \\ \hline \\ (I_{S} = 4.0 \text{ Adc}, \text{ V}_{GS} = 0 \text{ Vdc}, \\ dI_{S}/dt = 100 \text{ A}/\mu\text{s}) \\ \hline \\ \hline \\ \text{Reverse Recovery Stored Charge} \\ \hline \\ \hline \\ \begin{array}{c} - \\ - \\ \hline \\ \\ \hline \\ \\ \hline \\ \\ \end{array} \end{array} $			
(See Figure 14)(IS = 4.0 Adc, VGS = 0 Vdc, dIS/dt = 100 A/ $\mu$ s)IIReverse Recovery Stored Charge $Q_{RR}$	0.812		Vdc
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	557	557 —	ns
dl <sub>S</sub> /dt = 100 Å/µs) tb —   Reverse Recovery Stored Charge Q <sub>RR</sub> —	100	100 —	
Reverse Recovery Stored Charge	457	457 —	
	2.33	2.33 —	μC
INTERNAL PACKAGE INDUCTANCE		1	1

Internal Drain Inductance (Measured from contact screw on tab to center of die) (Measured from the drain lead 0.25" from package to center of die)	LD	_	3.5 4.5	_	nH
Internal Source Inductance (Measured from the source lead 0.25" from package to source bond pad)	LS	-	7.5	-	nH

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
Switching characteristics are independent of operating junction temperature.